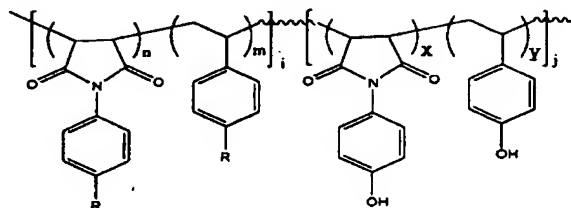


What is claimed is:

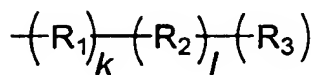
1. An organic gate insulating film comprising the organic insulating polymer as represented by the following Formula 1:

Formula 1



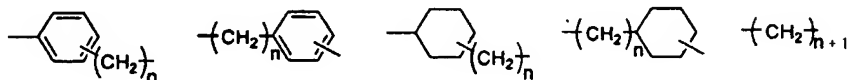
[Wherein, R is represented by the following Formula 2:

Formula 2



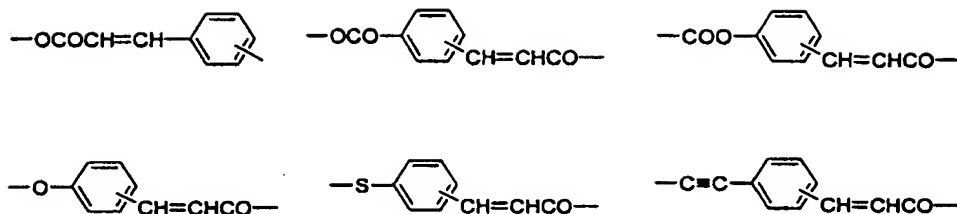
(Wherein, R<sub>1</sub> is selected from the following group I in which n is an integer of 0 to 10:

group I

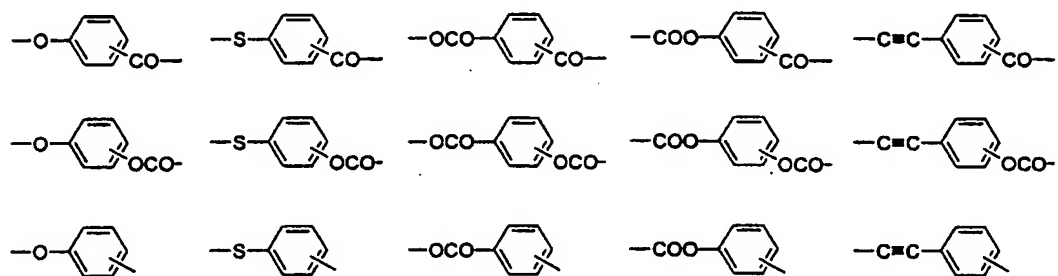


R<sub>2</sub> is a photo-alignment group selected from the groups II and III and, when l is 2 or more, at least one of R<sub>2</sub> is selected from the group II;

group II

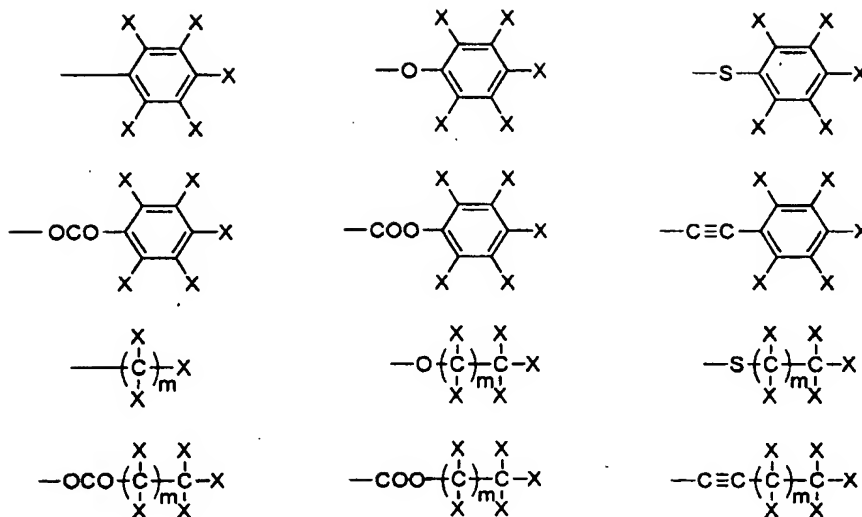


group III



5         $R_3$  is a hydrogen atom or is selected from the group IV  
in which X shows a hydrogen atom, an alkyl or alkoxy group  
of 1 to 13 carbon atoms, an aromatic group of 6 to 20 carbon  
atoms, a heteroaromatic group of 4 to 14 carbon atoms having  
a heteroatom contained in an aromatic ring,  $(OCH_2)_pCH_3$   
10 (wherein p is an integer of 0 to 12), F, or Cl, and m is an  
integer of 0 to 18:

group IV

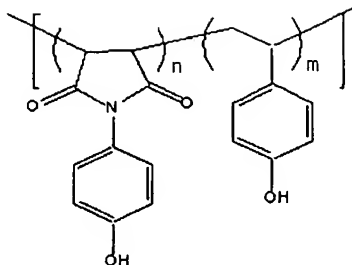


k is an integer of 0 to 3; l is an integer of 1 to 5;  
 and R<sub>1</sub> and R<sub>2</sub> are different respectively when R<sub>1</sub> and R<sub>2</sub>  
 5 includes a plurality of functional groups);

m is a real number of 0.3 to 0.7 and n is a real  
 number of 0.3 to 0.7, while the sum of m and n is 1; x is a  
 real number of 0.3 to 0.7 and y is a real number of 0.3 to  
 0.7, while the sum of x and y is 1; and i is a real number  
 10 of 0 to 1 and j is a real number of 0 to 1, while the sum of  
 i and j is 1].

2. The organic gate insulating film of Claim 1,  
 wherein the organic insulating polymer is represented by  
 15 Formula 11:

**Formula 11**



(wherein,  $m$  is a real number of 0.3 to 0.7,  $n$  is a real number of 0.3 to 0.7, and  $m+n$  is 1).

5

3. An organic Thin Film Transistor formed by laminating, sequentially on a substrate, a gate electrode, a gate insulating film, an organic active film, a source/drain electrode and a protection film, or laminating, sequentially  
10 on a substrate, a gate electrode, a gate insulating film, a source/drain electrode, an organic active film and a protection film, wherein the gate insulating film is the one set forth in Claim 1.

15

4. The organic Thin Film Transistor of Claim 3, wherein the organic gate insulating film is formed by printing, spin coating or dip coating.

20

5. The organic Thin Film Transistor of Claim 3, wherein the organic active film is selected from the group

consisting of pentacene, copper phthalocyanine, polythiophene, polyaniline, polyacetylene, polypyrrole, polyphenylenevinylene, and derivatives thereof.

5           6. The organic Thin Film Transistor of Claim 3,  
wherein the gate electrode is made of gold (Au), silver (Ag),  
nickel (Ni), indium tin oxide (ITO), aluminum (Al), or  
chromium (Cr) and the source and drain electrodes are made  
of gold (Au), silver (Ag), nickel (ni), indium tin oxide  
10 (ITO), or chromium (Cr).